

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	44673	semiconductor and ((thin adj film adj transistor) or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 16:28
L2	1266	1 and ((aluminum adj nitride) or aln)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 16:28
L3	1253	2 and (oxygen or o or carbon or c or (silicon adj (oxide or dioxide)) or sio or (silicon adj carbide) or sic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 16:29

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L1	44673	semiconductor and ((thin adj film adj transistor) or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 17:31
L2	21519	1 and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 17:31
L3	2110	2 and (laser adj irradiation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 17:32
L4	1747	3 and (silicon adj (oxide or dioxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 17:32
L5	1738	4 and crystal\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 17:33